

THERMAL TREATMENT
FOR BONDING INTERFACE STABILIZATION

ABSTRACT

The invention relates to a method for producing a structure comprising a thin layer of semiconductor material on a substrate, comprising the steps of:

- creating an area of embrittlement in the thickness of the donor substrate;
- bonding of the donor substrate with a support substrate;
- detaching the donor substrate at the level of the area of embrittlement, to transfer a part of the donor substrate onto the support substrate and to form the thin layer on the latter;
- thermal treating the structure obtained after detachment to stabilize the bonding interface between the thin layer and the substrate support, performed in such a way as to avoid the appearance of slip lines in the thin layer.

FIGURE 2c